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LIST OF REFERENCES CITED BY APPLICANT

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Kentaro NAKAJIMA, et al.

FILING DATE

September 12, 2003

GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
DM	AA	5,940,319	08/17/1999	M. DURLAM, et al.			
DM	AB	5,956,267	09/21/1999	A. T. HURST, et al.			
DM	AC	5,946,228	08/31/1999	D. W. ABRAHAM, et al.			
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AN							

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES	NO
DM	AO	WO 001/10172	02/24/2000	WIPO (with English Abstract and corr. JP 2002-522915)		X
DM	AP	2002-522915	07/23/2002	JAPAN		X
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DM	AV	S. TEHRANI, et al., Journal of Applied Physics, Magnetoresistive Magnetic Random Access Memory, vol. 85, no. 8, pages 5822-5827, "HIGH DENSITY SUBMICRON MAGNETORESISTIVE RANDOM ACCESS MEMORY (INVITED)", April 15, 1999	
DM	AW	R. SCHEUERLEIN, et al., IEEE International Solid-State Circuits Conference, ISSCC 2000 / Session 7 / TD: Emerging Memory & Device Technologies / Paper TA 7.2, pages 12B-129, "A 10ns READ AND WRITE NON-VOLATILE MEMORY ARRAY USING A MAGNETIC TUNNEL JUNCTION AND FET SWITCH IN EACH CELL", February 8, 2000	
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DM	AZ	K. INOMATA, et al., Jpn. J. Appl. Phys., vol. 36, part 2, no. 10B, pages L 1380-L 1383, "SPIN-DEPENDENT TUNNELING BETWEEN A SOFT FERROMAGNETIC LAYER AND HARD MAGNETIC NANOSIZE PARTICLES", October 15, 1997	<input type="checkbox"/> Additional References sheet(s) attached

Examiner

Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.